Electronic Supplementary Material (ESI) for RSC Advances.

Supporting Information

One-step preparation of graphene oxide-poly(3,4ethylenedioxythiophene) composite films for nonvolatile rewritable memory

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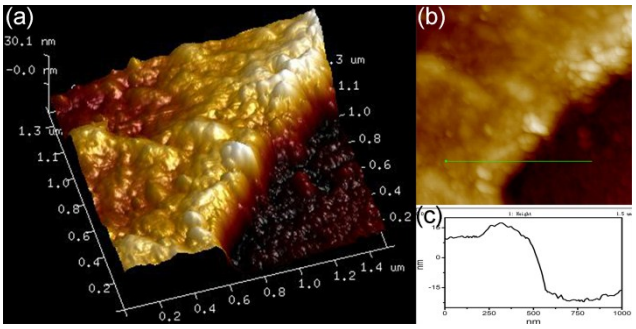

Fig. S1 (a) The AFM 3D height image of GO-PEDOT composite films on ITO substrate. (b) The AFM 2D height image of GO-PEDOT composite films on ITO substrate. (c) The height profile which is taken along the green line in (b). It is measured that the thickness of the GO-PEDOT composite films is about 35 nm.

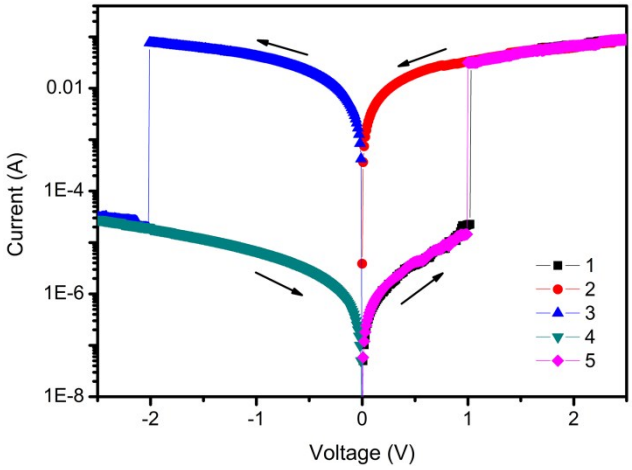

Fig. S2 The I-V characteristics of the ITO/GO-PEDOT/Al device under vacuum. The result shows that the ON/OFF current ratio of the device under vacuum is 7×10^3 at 0.3 V and the turn-on voltage is 1 V.